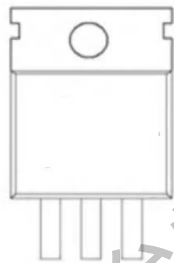


**TMG130N10HP****N-Channel Enhancement Mosfet****General Description**

- Low  $R_{DS(ON)}$
- RoHS and Halogen-Free Compliant

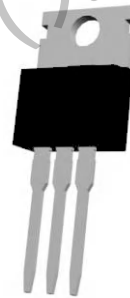
**Applications**

- Load switch
- PWM

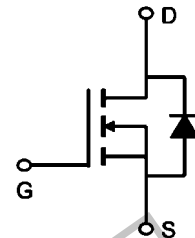
**General Features** $V_{DS} = 100V$   $I_D = 130A$  $R_{DS(ON)} = 4.2m\Omega$  (typ.) @  $V_{GS} = 10V$ 100% UIS Tested  
100%  $R_g$  Tested

Marking: G130N10

P:TO-220AB



G D S

**Absolute Maximum Ratings ( $T_A = 25^\circ C$  unless otherwise noted)**

Characteristics	Symbol	Value	Unit
Drain-Source Voltage	$V_{DS}$	100	V
Gate-Source Voltage	$V_{GS}$	$\pm 20$	V
Continue Drain Current	$I_D$	130	A
Pulsed Drain Current (Note1)	$I_{DM}$	481	A
Power Dissipation	$P_D$	210	W
Single Pulse Avalanche Energy (Note1)	$E_{AS}$	750	mJ
Operating Temperature Range	$T_J$	175	$^\circ C$
Storage Temperature Range	$T_{STG}$	-55 to +175	$^\circ C$
Thermal Resistance, Junction to Case	$R_{\theta JC}$	0.71	$^\circ C/W$
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	55	$^\circ C/W$

**TMG130N10HP**

**N-Channel Enhancement Mosfet**

Electrical Characteristics at Tc=25°C unless otherwise specified

Characteristics	Test Condition	Symbol	Min	Typ	Max	Unit
Drain-Source Breakdown Voltage	$V_{GS} = 0 V, I_D = 250 \mu A$	$BV_{DSS}$	100	-	-	V
Drain-Source Leakage Current	$V_{DS} = 100 V, V_{GS} = 0 V$	$I_{DSS}$	-	-	1	$\mu A$
Gate Leakage Current	$V_{GS} = \pm 20 V, V_{DS} = 0 V$	$I_{GSS}$	-	-	$\pm 100$	nA
Gate-Source Threshold Voltage	$V_{DS} = V_{GS}, I_D = 250 \mu A$	$V_{GS(th)}$	2	3	4	V
Drain-Source On-State Resistance (Note 3)	$V_{GS} = 10 V, I_D = 20 A$	$R_{DS(on)}$	-	4.2	5.3	m $\Omega$
Forward Transconductance	$V_{DS} = 5 V, I_D = 65 A$	gfs	-	130	-	S
Input Capacitance	$V_{DS}=50 V, V_{GS}=0V, f=1MHz$	$C_{iss}$	-	4350	-	pF
Output Capacitance		$C_{oss}$	-	2150	-	pF
Reverse Transfer Capacitance		$C_{rss}$	-	220	-	pF
Turn-on Delay Time(Note2)	$V_{DD}=50 V, V_{GS}=10 V, RG=3 \Omega, I_D=65A$	$t_{d(ON)}$	-	23	-	ns
Rise Time(Note2)		$t_r$	-	15	-	ns
Turn-Off Delay Time(Note2)		$t_{d(OFF)}$	-	48	-	ns
Fall Time(Note2)		$t_f$	-	16	-	ns
Total Gate Charge(Note2)	$V_{DS}=50V, V_{GS}=10V, I_D=65A$	$Q_G$	-	110	-	nC
Gate to Source Charge(Note2)		$Q_{GS}$	-	33	-	nC
Gate to Drain Charge(Note2)		$Q_{GD}$	-	30	-	nC

Source-Drain Diode Characteristics at Ta=25°C unless otherwise specified

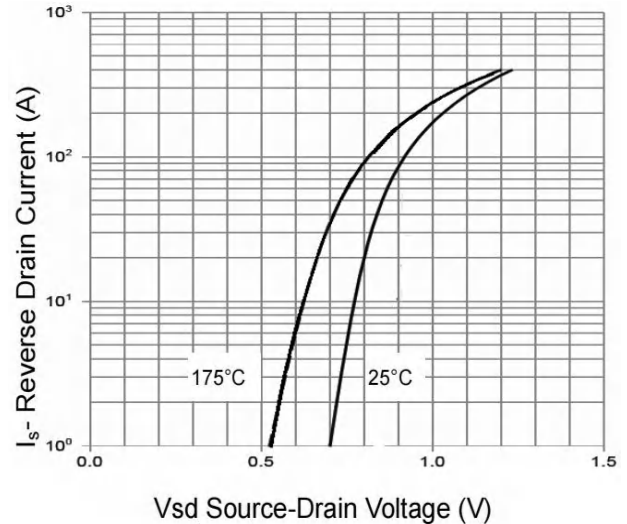
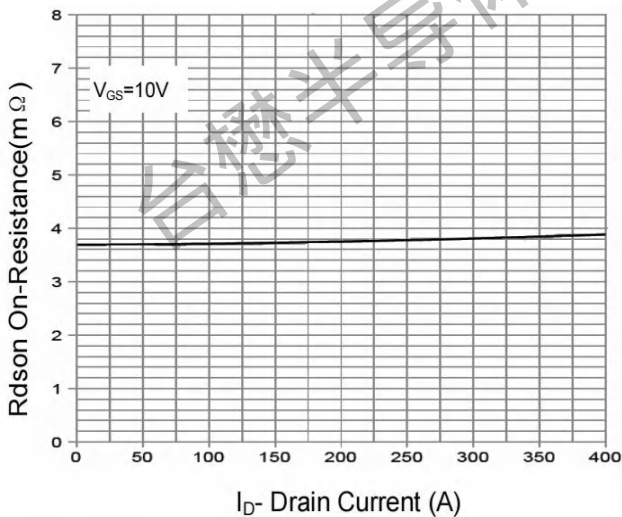
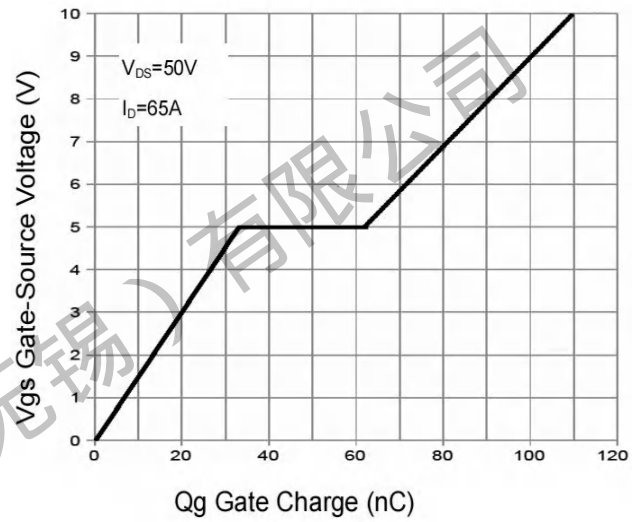
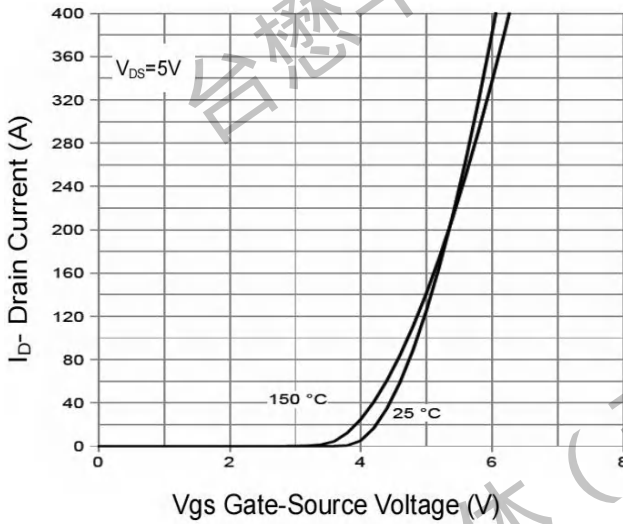
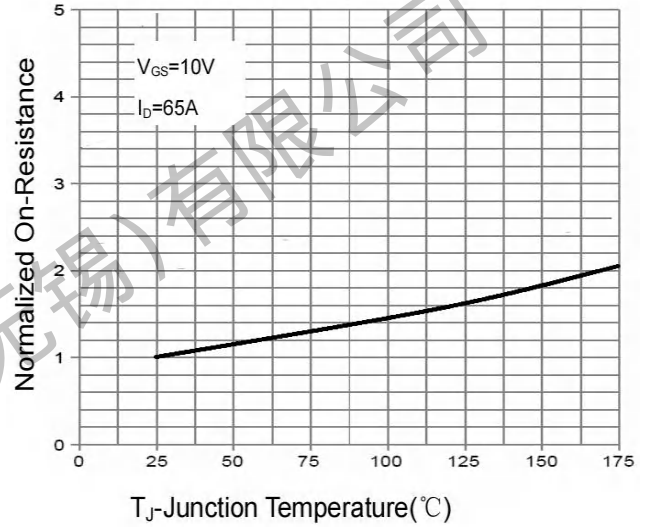
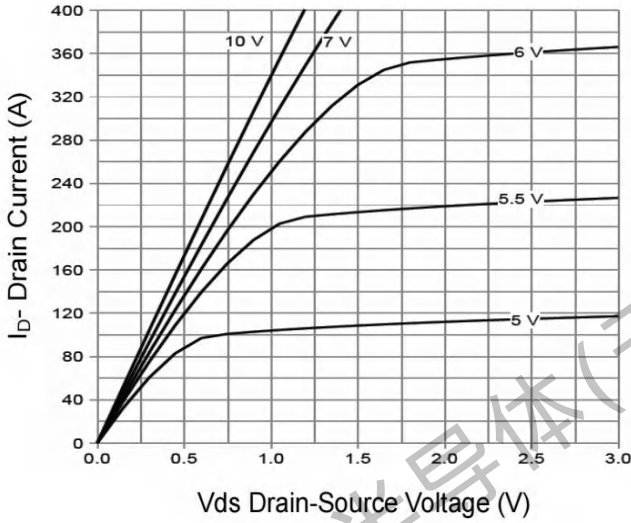
Characteristics	Test Condition	Symbol	Min.	Typ.	Max.	Unit
Maximun Body-Diode Continuous Current		$I_S$	-	-	130	A
Drain-Source Diode Forward Voltage	$V_{GS}=0V, I_S=40A, T_J=25^\circ C$	$V_{SD}$	-	0.86	1.2	V
Reverse Recovery Time(Note2)	$T_J = 25^\circ C, I_F = 65A$	trr	-	70	-	ns
Reverse Recovery Charge(Note2)	$di / dt = 100 A/\mu s$	Qrr	-	117	-	nC



**TMG130N10HP**

**N-Channel Enhancement Mosfet**

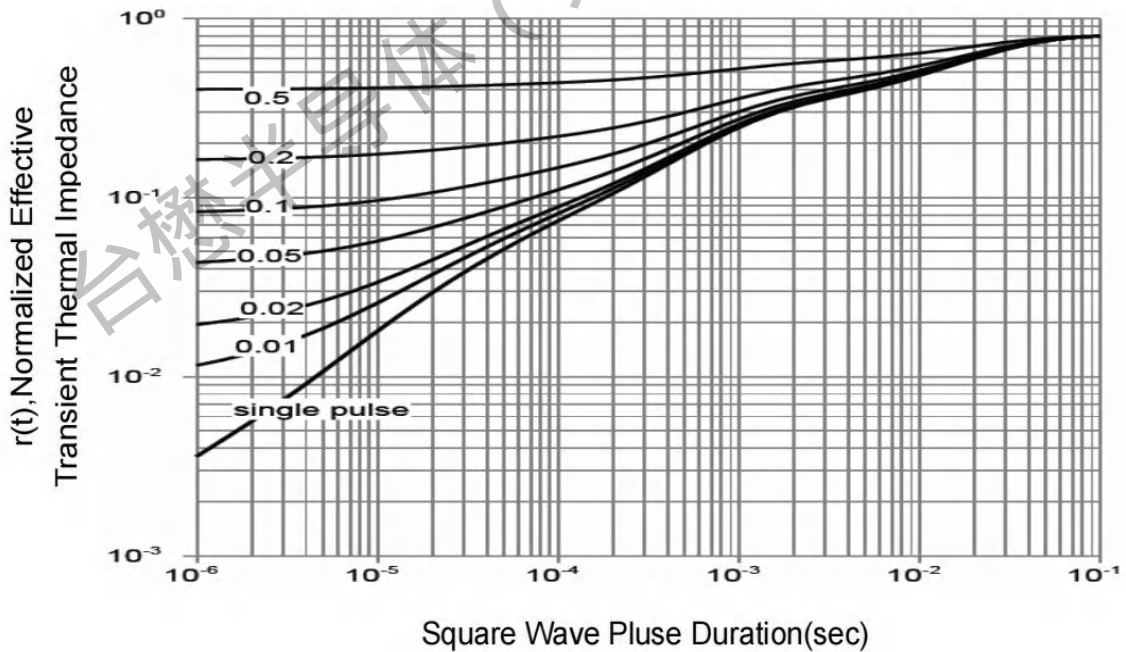
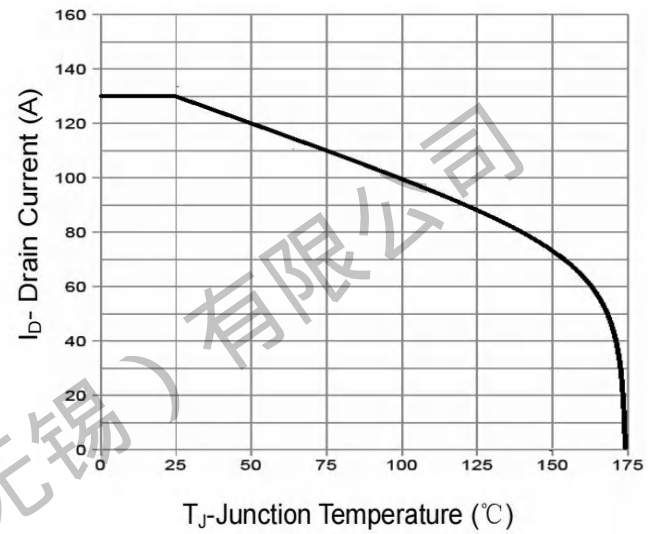
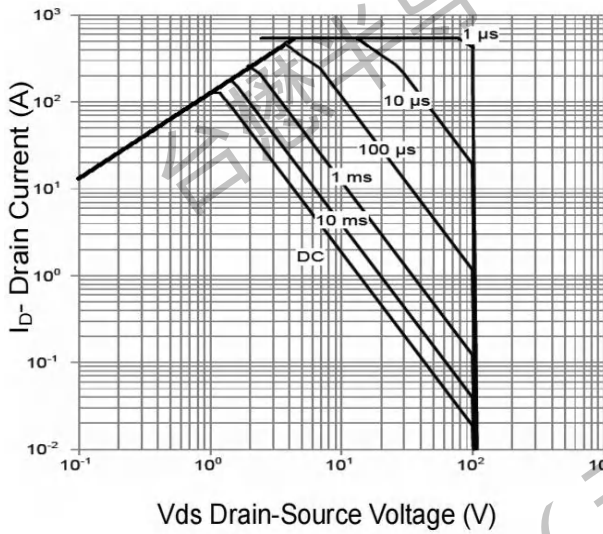
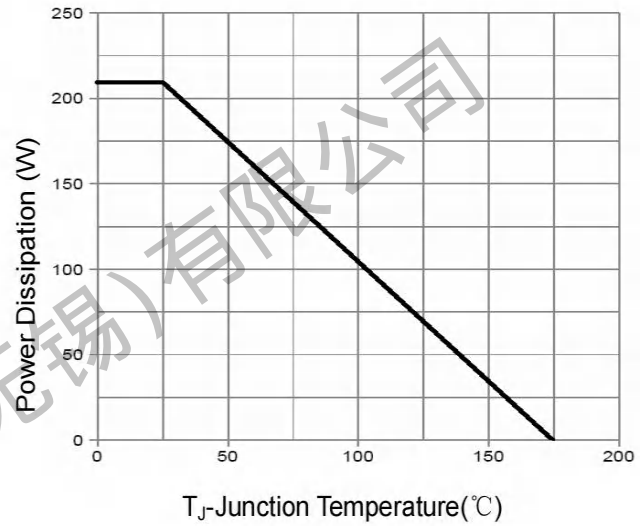
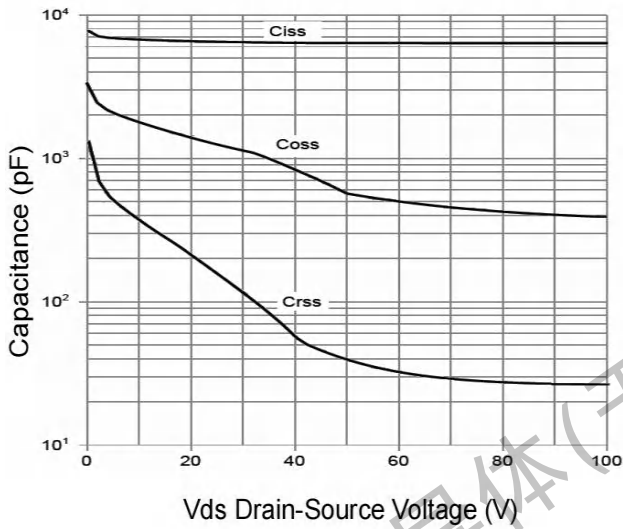
Typical Characteristics: ( $T_c=25^\circ\text{C}$  unless otherwise noted)





TMG130N10HP

N-Channel Enhancement Mosfet

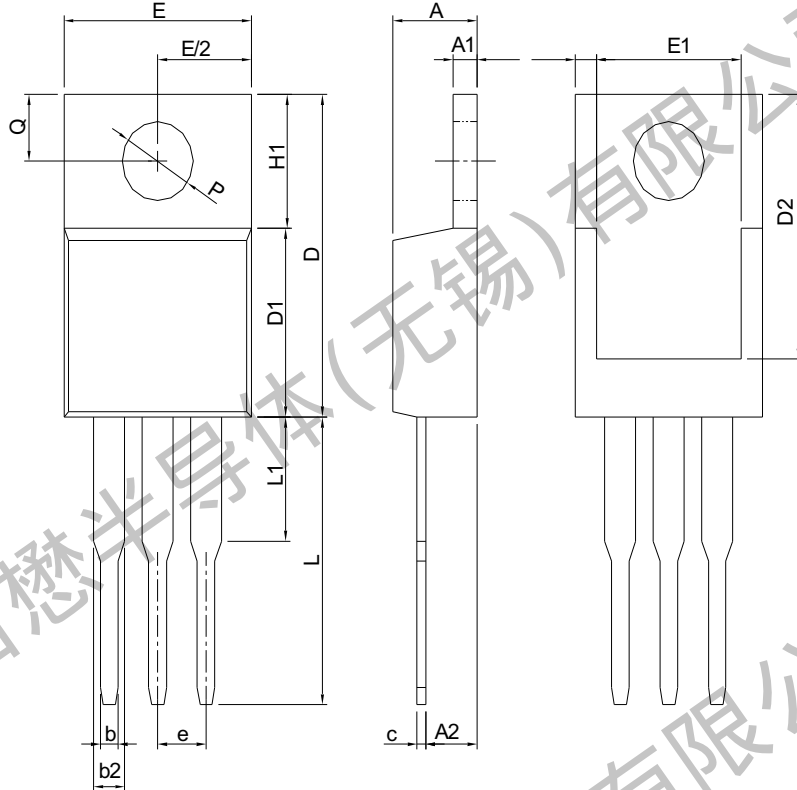




# TMG130N10HP

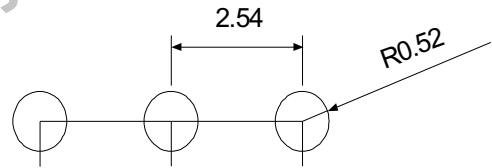
# N-Channel Enhancement Mosfet

## Package Mechanical Data: TO-220AB



SYMBOL	TO-220			
	MILLIMETERS		INCHES	
	MIN.	MAX.	MIN.	MAX.
A	3.56	4.83	0.140	0.190
A1	0.51	1.40	0.020	0.055
A2	2.03	2.92	0.080	0.115
b	0.38	1.02	0.015	0.040
b2	1.14	1.78	0.045	0.070
c	0.36	0.61	0.014	0.024
D	14.22	16.51	0.560	0.650
D1	8.38	9.02	0.330	0.355
D2	12.19	13.65	0.480	0.537
E	9.65	10.67	0.380	0.420
E1	6.86	8.89	0.270	0.350
e	2.54 BSC		0.100 BSC	
H1	5.84	6.86	0.230	0.270
L	12.70	14.73	0.500	0.580
L1	-	6.35	-	0.250
P	3.53	4.09	0.139	0.161
Q	2.54	3.43	0.100	0.135

### RECOMMENDED LAND PATTERN



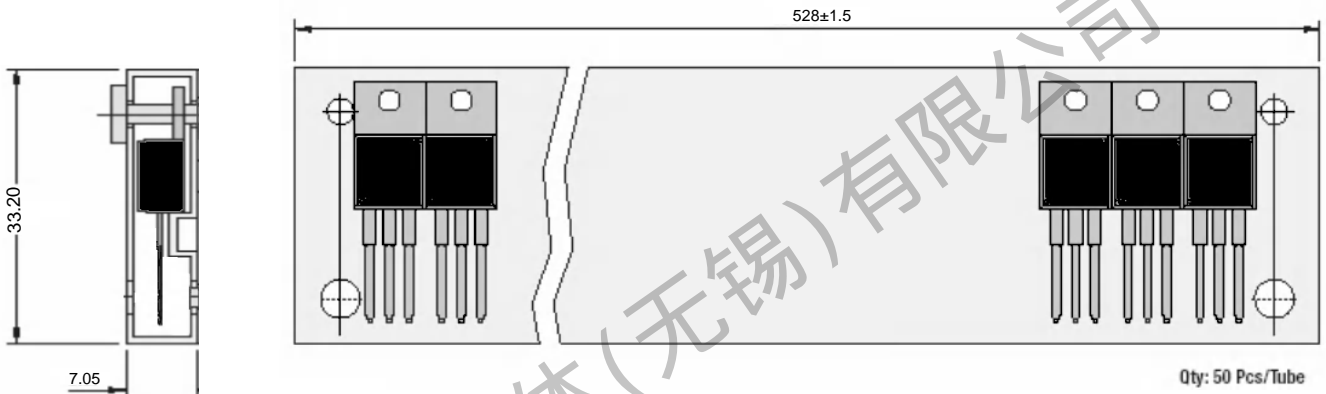
UNIT: mm

Note: Follow JEDEC TO-220 AB.



# TMG130N10HP

## N-Channel Enhancement Mosfet



All Dimensions are in mm

### 1. TO-220AB Packaging

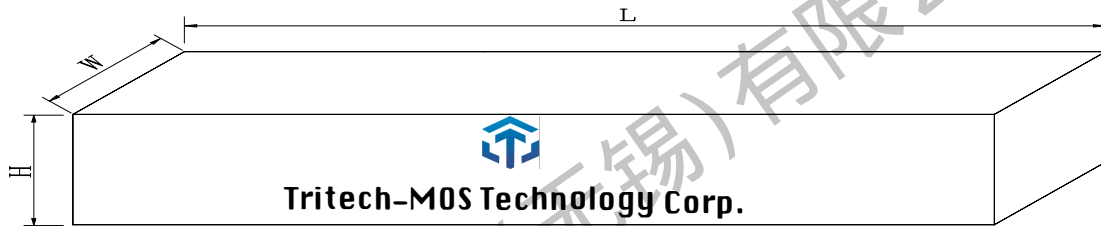
Package	Packing Form	Quantity		
		Tube	Inner Box [kpcs]	Outbox [kpcs]
TO-220AB	Tube Tape	50	5	1



**TMG130N10HP**

**N-Channel Enhancement Mosfet**

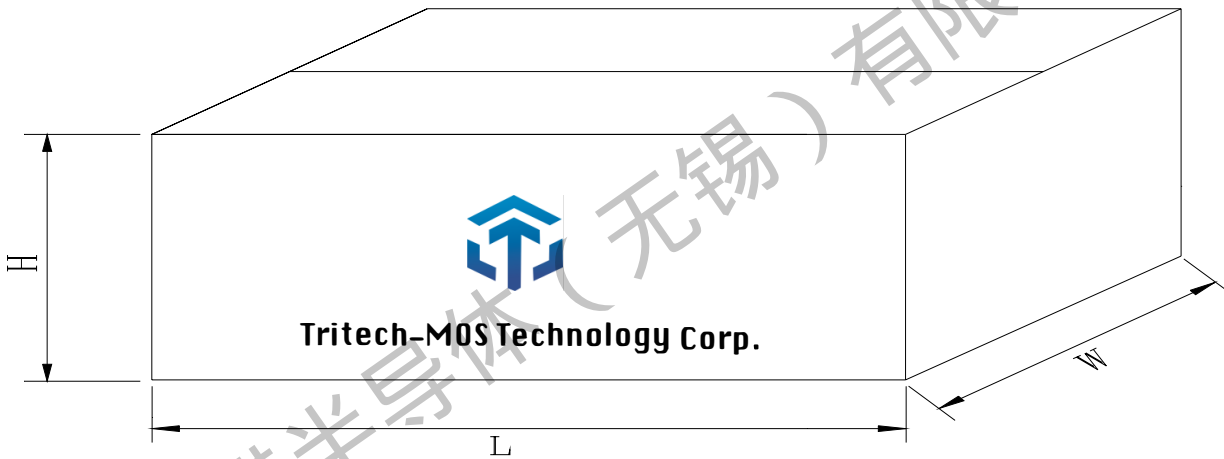
**Inner Box**



**Dimension : 580 (L)×154(W) ×49(H) mm**

**Quantity : 50 ×20Ea = 1Kpcs**

**Outer Box**



**Dimension : 595(L)×285(W) ×185(H) mm**

**Quantity : 1K×5Ea = 5Kpcs**



### Important Notices and Disclaimers

- Tritech-MOS Technology Corp. reserves the right to change this document, its products, and specifications at any time without prior notice.
- Before final design, purchase, or use, customers should obtain and confirm the latest product information and specifications.
- Tritech-MOS Technology Corp. makes no warranties, representations or warranties regarding the suitability of its products for any specific purpose, and Tritech-MOS Technology Corp. does not assume any responsibility for application assistance or customer product design.
- Tritech-MOS Technology Corp. does not guarantee or assume any responsibility for the purchase or use of any unexpected or unauthorized products.
- Any intellectual property rights of Tritech-MOS Technology Corp. are not licensed through implicate or other means.
- Products of Tritech-MOS Technology Corp. are not included as critical components in life support equipment or systems without explicit written approval from Tritech-MOS Technology Corp.

Revision history:

Date	Rev	Description	Page
2024.06.08	24.06	Original	